

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of manufacturing an internal filter, comprising:

- providing a first substrate;
- providing a second substrate;
- forming a plurality of first passages in the first substrate;
- forming a plurality of second passages in the first substrate;
- forming a plurality of third passages in one of the first substrate and the second substrate; and

placing the first and second substrates adjacent to each other, such that the plurality of third passages extend between and directly connect to the first and second passages and fluidly connect the first and second passages such that particles having a size greater than that which can pass through the third passages are filtered from the fluid when the fluid flows through the first passages, into and through the third passages, and into the second passages, wherein

the internal filter comprises the plurality of first passages, the plurality of second passages, and the plurality of third passages.

2. (Original) The method of claim 1, wherein forming the first and second passages comprises forming the first and second passages using at least one of an orientation-dependent etching technique, a non orientation-dependent etching technique, and a reactive ion etching technique.

3. (Original) The method of claim 2, wherein forming the third passages comprises forming the third passages using at least one of an orientation-dependent etching

technique, a non orientation-dependent etching technique, and a reactive ion etching technique.

4. (Withdrawn) The method of claim 1, wherein:

forming the first and second passages in the first substrate comprises forming at least some of the first and second passages such that those ones of the first and second passages extend completely through the first substrate.

5. (Withdrawn) The method of claim 4, further comprising placing a third substrate adjacent to an outer surface of the first substrate.

6. (Withdrawn) The method of claim 4, wherein forming the plurality of third passages comprises forming the plurality of third passages in the second substrate.

7. (Withdrawn) The method of claim 6, wherein forming the plurality of third passages in the second substrate comprises forming at least some of the third passages such that those ones of the third passages extend completely through the second substrate.

8. (Withdrawn) The method of claim 7, further comprising placing a third substrate adjacent to an outer surface of the second substrate.

9-19. (Canceled)

20. (New) A method of manufacturing an internal filter, comprising:

providing a first substrate;

providing a second substrate;

forming a plurality of first passages in the first substrate;

forming a plurality of second passages in the first substrate such that the second passages are interleaved with the first passages;

forming a plurality of third passages in one of the first substrate and the second substrate; and

placing the first and second substrates adjacent to each other, such that

the plurality of third passages extend between the first and second passages and fluidly connect the first and second passages such that particles having a size greater than that which can pass through the third passages are filtered from the fluid when the fluid flows through the first passages, into and through the third passages, and into the second passages.

21. (New) The method of claim 20, wherein forming the first and second passages comprises forming the first and second passages using at least one of an orientation-dependent etching technique, a non orientation-dependent etching technique, and a reactive ion etching technique.

22. (New) The method of claim 21, wherein forming the third passages comprises forming the third passages using at least one of an orientation-dependent etching technique, a non orientation-dependent etching technique, and a reactive ion etching technique.

23. (New) The method of claim 20, wherein:
forming the first and second passages in the first substrate comprises forming at least some of the first and second passages such that those ones of the first and second passages extend completely through the first substrate.

24. (New) The method of claim 23, further comprising placing a third substrate adjacent to an outer surface of the first substrate.

25. (New) The method of claim 23, wherein forming the plurality of third passages comprises forming the plurality of third passages in the second substrate.

26. (New) The method of claim 6, wherein forming the plurality of third passages in the second substrate comprises forming at least some of the third passages such that those ones of the third passages extend completely through the second substrate.

27. (New) The method of claim 26, further comprising placing a third substrate adjacent to an outer surface of the second substrate.

28. (New) A method of manufacturing an internal filter, comprising:

providing a first substrate;
providing a second substrate;
forming a plurality of first passages in the first substrate;
forming a plurality of second passages in the first substrate;
forming a plurality of third passages in one of the first substrate and the second substrate; and

placing the first and second substrates adjacent to each other, such that the plurality of third passages extend between the first and second passages and fluidly connect the first and second passages such that particles having a size greater than that which can pass through the third passages are filtered from the fluid when the fluid flows through the first passages, into and through the third passages, and into the second passages, and

every fluidic connection between a first passage and a second passage comprises two or more third passages, wherein

the internal filter comprises the plurality of first passages, the plurality of second passages, and the plurality of third passages.

29. (New) The method of claim 28, wherein forming the first and second passages comprises forming the first and second passages using at least one of an orientation-dependent etching technique, a non orientation-dependent etching technique, and a reactive ion etching technique.

30. (New) The method of claim 29, wherein forming the third passages comprises forming the third passages using at least one of an orientation-dependent etching technique, a non orientation-dependent etching technique, and a reactive ion etching technique.

31. (New) The method of claim 28, wherein:

forming the first and second passages in the first substrate comprises forming at least some of the first and second passages such that those ones of the first and second passages extend completely through the first substrate.